

# Mahmut Tosun

## List of Publications by Year in descending order

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18  
papers

4,633  
citations

471061

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887659

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18  
docs citations

18  
times ranked

6906  
citing authors

| #  | ARTICLE   | IF   | CITATIONS |
|----|---|------|-----------|
| 1  | Nanoscale Junction Formation by Gas-Phase Monolayer Doping. ACS Applied Materials & Interfaces, 2017, 9, 20648-20655.                             | 4.0  | 22        |
| 2  | Gold-Mediated Exfoliation of Ultralarge Optoelectronically-Perfect Monolayers. Advanced Materials, 2016, 28, 4053-4058.                           | 11.1 | 307       |
| 3  | 2D-2D tunneling field-effect transistors using WSe <sub>2</sub> /SnSe <sub>2</sub> heterostructures. Applied Physics Letters, 2016, 108, .        | 1.5  | 252       |
| 4  | Air-Stable n-Doping of WSe <sub>2</sub> by Anion Vacancy Formation with Mild Plasma Treatment. ACS Nano, 2016, 10, 6853-6860.                     | 7.3  | 202       |
| 5  | Monolithic 3D CMOS Using Layered Semiconductors. Advanced Materials, 2016, 28, 2547-2554.   | 11.1 | 107       |
| 6  | Lithium Fluoride Based Electron Contacts for High Efficiency n-Type Crystalline Silicon Solar Cells. Advanced Energy Materials, 2016, 6, 1600241. | 10.2 | 134       |
| 7  | Direct growth of single-crystalline III-V semiconductors on amorphous substrates. Nature Communications, 2016, 7, 10502.                          | 5.8  | 45        |
| 8  | 2D layered materials: From materials properties to device applications. , 2015, , .   |      | 9         |
| 9  | Dual-Gated MoS <sub>2</sub> /WSe <sub>2</sub> van der Waals Tunnel Diodes and Transistors. ACS Nano, 2015, 9, 2071-2079.                          | 7.3  | 560       |
| 10 | MoS <sub>2</sub> Heterojunctions by Thickness Modulation. Scientific Reports, 2015, 5, 10990.   | 1.6  | 93        |
| 11 | Oriented Growth of Gold Nanowires on MoS <sub>2</sub> . Advanced Functional Materials, 2015, 25, 6257-6264.                                       | 7.8  | 21        |
| 12 | Air stable n-doping of WSe <sub>2</sub> by silicon nitride thin films with tunable fixed charge density. APL Materials, 2014, 2, .                | 2.2  | 76        |
| 13 | Field-Effect Transistors Built from All Two-Dimensional Material Components. ACS Nano, 2014, 8, 6259-6264.  | 7.3  | 582       |
| 14 | Air-Stable Surface Charge Transfer Doping of MoS <sub>2</sub> by Benzyl Viologen. Journal of the American Chemical Society, 2014, 136, 7853-7856. | 6.6  | 593       |
| 15 | Air Stable p-Doping of WSe <sub>2</sub> by Covalent Functionalization. ACS Nano, 2014, 8, 10808-10814.  | 7.3  | 208       |
| 16 | MoS <sub>2</sub> P-type Transistors and Diodes Enabled by High Work Function MoO <sub>x</sub> Contacts. Nano Letters, 2014, 14, 1337-1342.        | 4.5  | 487       |
| 17 | High-Gain Inverters Based on WSe <sub>2</sub> Complementary Field-Effect Transistors. ACS Nano, 2014, 8, 4948-4953.                               | 7.3  | 284       |
| 18 | Degenerate n-Doping of Few-Layer Transition Metal Dichalcogenides by Potassium. Nano Letters, 2013, 13, 1991-1995.                                | 4.5  | 651       |